

[PHOTOLITHOGRAPHY PROCRSS FOR MASK ROM CODING]

Abstract of Disclosure

A photolithography process for Mask ROM coding is described. A substrate is provided having a memory array thereon. A first photoresist layer is formed on the substrate with first line/space patterns, which include trenches having different lengths. A second photoresist layer is formed on the substrate with second line/space patterns. The second line/space patterns comprise a plurality of linear patterns and linear spaces that are arranged regularly, and have an orientation different from that of the first line/space pattern. Consequently, a plurality of uniform coding windows are defined by the first line/space patterns and the second line/space patterns.

Figures